



MMBT2369A

NPN GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 15 Volts **POWER** 225 mWatts

SOT-23

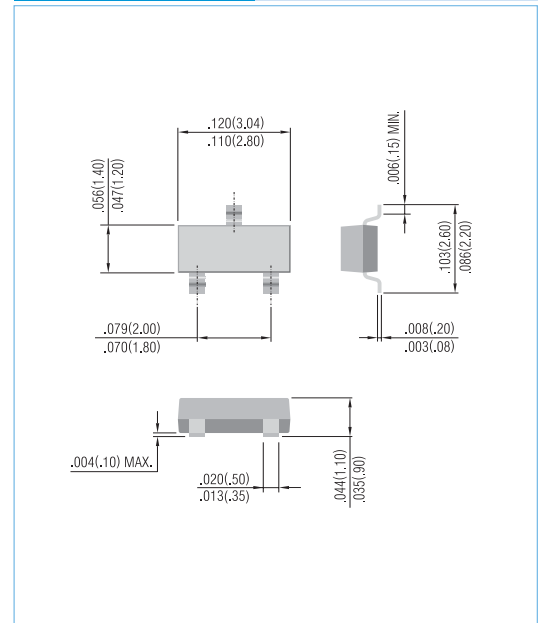
Unit: inch (mm)

FEATURES

- NPN epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 15V$
- Collector current $I_C = 200mA$
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: SOT-23, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.008 gram
- Marking: M3B



ABSOLUTE RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	15	V
Collector - Base Voltage	V_{CBO}	40	V
Emitter - Base Voltage	V_{EBO}	4.5	V
Collector Current - Continuous	I_C	200	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Thermal Resistance , Junction to Ambient	$R_{\theta A}$	556	$^{\circ}C/W$
Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$

Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.



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ELECTRICAL CHARACTERISTICS

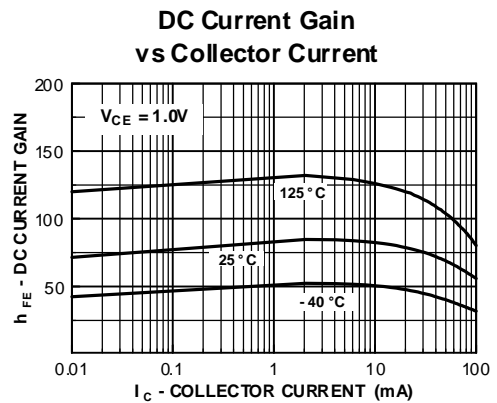
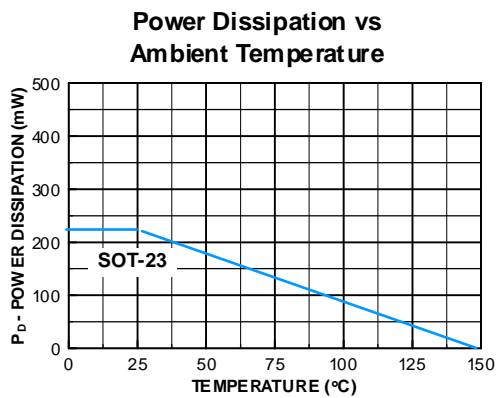
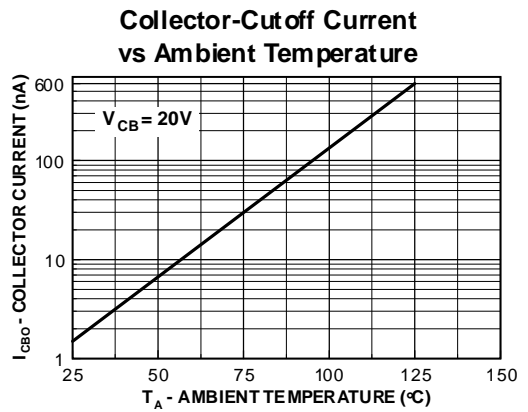
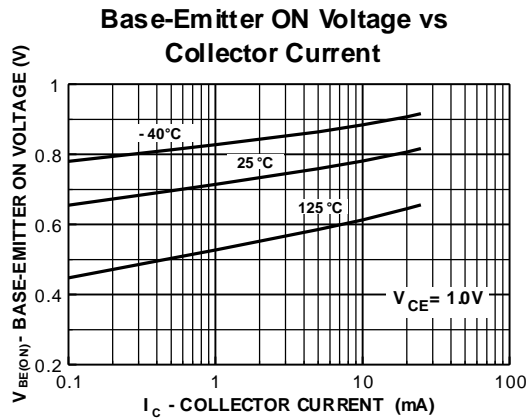
PARAMETER	Symbol	Test Condition	MIN.	MAX.	Units
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	15	-	V
Collector - Emitter Breakdown Voltage	$V_{(BR)CES}$	$I_C=10mA, I_B=0$	40	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=10\mu A, I_E=0$	40	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=10\mu A, I_C=0$	4.5	-	V
Collector Cutoff Current	I_{CBO}	$V_{CB}=20V, I_E=0$ $V_{CB}=20V, I_E=0, T_A=125^\circ C$		0.4 30	μA μA
ON CHARACTERISTICS					
DC Current Gain (Note 2)	h_{FE}	$I_C=10mA, V_{CE}=1.0V$ $I_C=10mA, V_{CE}=0.35V, T_A=-55^\circ C$ $I_C=30mA, V_{CE}=0.4V$ $I_C=100mA, V_{CE}=1.0V$	40 40 30 20	120	-
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=10mA, I_B=1.0mA, T_A=125^\circ C$ $I_C=30mA, I_B=3.0mA$ $I_C=100mA, I_B=10mA$	-	0.2 0.3 0.25 0.5	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$ $I_C=10mA, I_B=1.0mA, T_A=-55^\circ C$ $I_C=10mA, I_B=1.0mA, T_A=125^\circ C$ $I_C=30mA, I_B=3.0mA$ $I_C=100mA, I_B=10mA$	0.7 0.59	0.85 1.02 1.15 1.6	V
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{OBO}	$V_{CB}=5V, I_E=0, f=1MHz$	-	4.0	pF
Input Capacitance	C_{IBO}	$V_{CB}=0.5V, I_C=0, f=1MHz$	-	5.0	pF
Small-Signal Current Gain	h_{FE}	$I_C=10mA, V_{CE}=10V,$ $R_C=2.0k\Omega, f=100MHz$	5.0	-	-
SWITCHING CHARACTERISTICS					
Storage Time	t_s	$I_B1=I_B2=I_C=10mA$	-	13	ns
Turn-On Time	t_{on}	$V_{CC}=3V, I_C=10mA$ $I_B1=3.0mA$	-	12	ns
Turn-Off Time	t_{off}	$V_{CC}=3V, I_C=10mA$ $I_B1=3.0mA, I_B2=1.5mA$	-	18	ns

Note 2: Pulse Test: Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2.0\%$.



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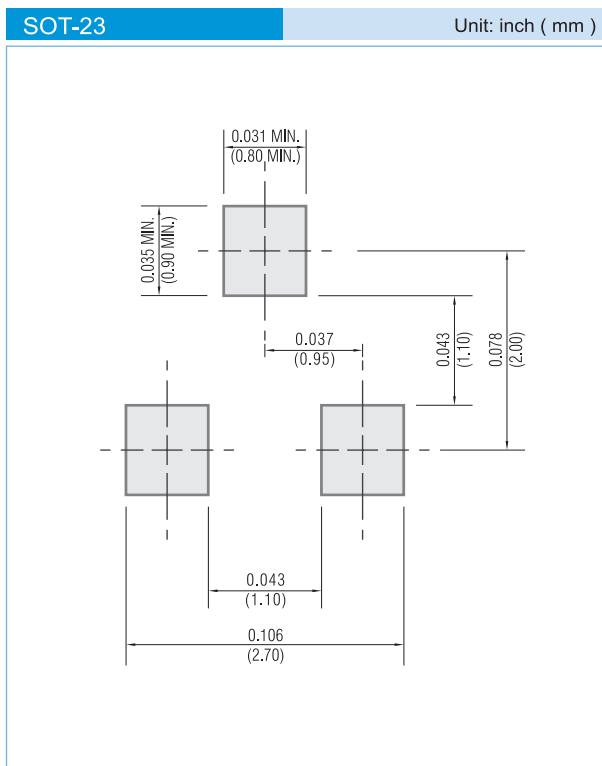
ELECTRICAL CHARACTERISTICS CURVE





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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 12K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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